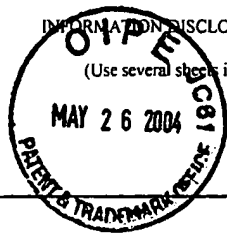


INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

MAY 26 2004



Docket Number (Optional) FUJI:200A)

SERIAL NO.: 10/646,590

APPLICANT(s) Takashi KOBAYASHI et al.

FILING DATE: August 22, 2003

Group Art Unit 2826

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
VAMS	US	4,602,266 A	7/86	Coe	357	20	
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							YES	NO
VAMS	GB	1427014 A	3/76	GB				

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED		
<i>[Signature]</i>	9-1-04		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <small>(Use several sheets if necessary)</small>				Docket Number (Optional) FUJI: 200A		Application Number 10/646,590	
				Applicant(s) Takashi KOBAYASHI et al.			
				Filing Date August 22, 2003		Group Art Unit 2811	
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VAMS	"Optimization and Surface Charge Sensitivity of High-Voltage Blocking Structures with Shallow Junctions"; Hamza Yilmaz; July 1991; IEEE Transactions on Electron Devices, Vol. 38, No. 7; pages 1666-1675.						
VAMS	"A Parametric Study of Power Mosfets"; Chenming Hu; Proceedings of the Conference of Rec. Power Electronics Specialists, 1979 IEEE; pages 385-395.						
EXAMINER	Victor A. Mandala			DATE CONSIDERED 9-1-04			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							